



### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	l <sub>D</sub> max T <sub>A</sub> = +25°C
-30V	65mΩ @ V <sub>GS</sub> = -10V	-3.8A
-30 V	99mΩ @ V <sub>GS</sub> = -4.5V	-3.0A

### Description

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

SOT23

Top View

### Applications

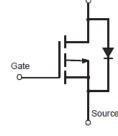
- Backlighting
- Power Management Functions
- **DC-DC Converters**

### Features and Benefits

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

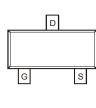
### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



Equivalent Circuit

Drain



Top View **Pin Configuration** 

## Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMP3099L-7	Standard	SOT23	3000/Tape & Reel
DMP3099L-13	Standard	SOT23	10000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

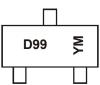
Notes:

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

## Marking Information



D99= Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

#### Date Code Key

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Manth		Feb	Mar	<b>A</b>	Mav	l	Jul	A	Sam	Oct	Nov	Dee
Month	Jan	гер	war	Apr	way	Jun	Jui	Aug	Sep	UCL	NOV	Dec



### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteris	tic		Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage	_	V <sub>GSS</sub>	±20	V	
Drain Current (Note 5) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	-3.8 -2.9	A
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-11	A

## **Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	PD	1.08	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>θJA</sub>	115	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Cumphed	Mila	T. m	Max	11	Test Condition	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)			1	1			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			-800	nA	$V_{DS}$ = -30V, $V_{GS}$ = 0V	
Gate-Source Leakage	I <sub>GSS</sub>		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0		-2.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance				65	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.8A	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_		99	11122	$V_{GS}$ = -4.5V, $I_{D}$ = -3.0A	
Forward Transfer Admittance	Y <sub>fs</sub>	_	3.6	_	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -2.7A	
Diode Forward Voltage (Note 6)	V <sub>SD</sub>	_	_	-1.26	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2.7A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	563	_	pF	(-25)(-)(-20)(-20)(-20)(-20)(-20)(-20)(-20)(	
Output Capacitance	Coss	_	48	_	pF	−V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, −f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		41		pF		
Gate Resistance	R <sub>G</sub>	_	10.3	_	Ω	$V_{GS} = 0V V_{DS} = 0V, f = 1MHz$	
SWITCHING CHARACTERISTICS (Note 8)							
Total Gate Charge	Qg	—	5.2	_		V <sub>DS</sub> = -15V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.8A	
		_	11	_	nC	(-45)(-40)(-40)(-40)(-40)(-40)(-40)(-40)(-40	
Gate-Source Charge	Q <sub>gs</sub>		1.7			V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.8A	
Gate-Drain Charge	Q <sub>qd</sub>		1.9			ID3.6A	
Turn-On Delay Time	t <sub>d(on)</sub>		4.8				
Rise Time	tr		5.0			V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V,	
Turn-Off Delay Time	t <sub>d(off)</sub>	—	31	—	ns	$I_{\rm D}$ = -1A, R <sub>G</sub> = 6.0Ω	
Fall Time	t <sub>f</sub>		15				

5. Device mounted on FR-4 PCB on 2 oz., 0.5 in.<sup>2</sup> copper pads and t  $\leq$ 5 sec. 6. Pulse width  $\leq$ 10µS, Duty Cycle  $\leq$ 1%. Notes:

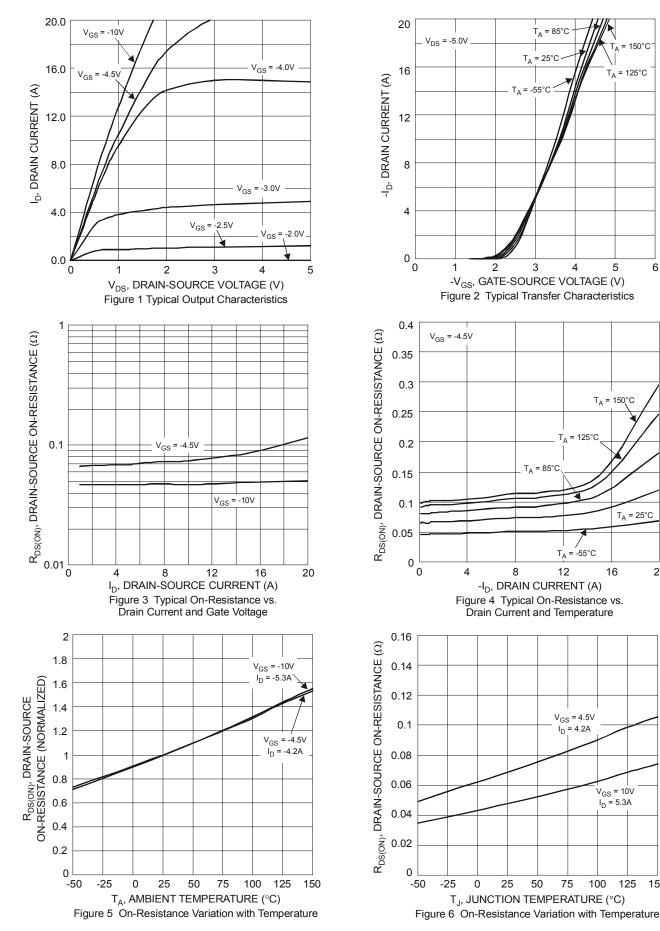
7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to production testing.



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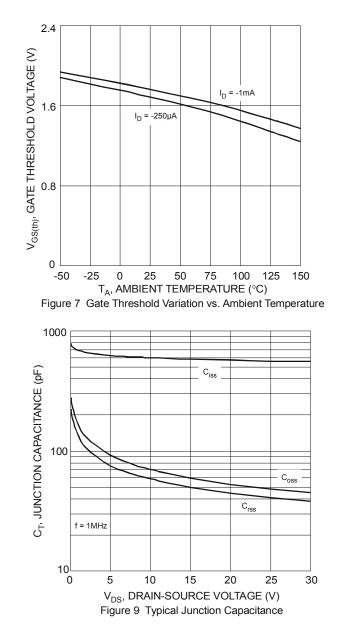
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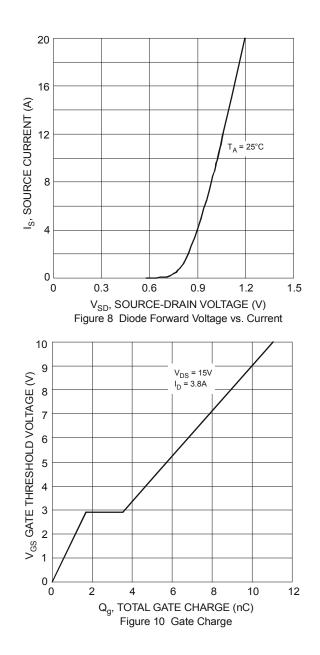


DMP3099L Document number: DS36081 Rev. 3 - 2 150

<sup>3</sup> of 6 Downloaded From Oneyac.com



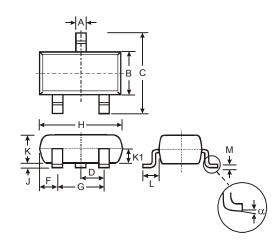






# Package Outline Dimensions

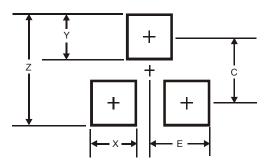
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
в	1.20	1.40	1.30					
C	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
<b>ر</b>	0.013	0.10	0.05					
κ	0.903	1.10	1.00					
K1	-	-	0.400					
L	0.45	0.61	0.55					
Μ	0.085	0.18	0.11					
α	0°	8°	-					
All	Dimens	ions in	mm					

## Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)				
Z	2.9				
Х	0.8				
Y	0.9				
С	2.0				
E	1.35				



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